In re: David B. Slater, Jr. et al. Application Serial No.: 10/659,241

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In the Specification:

Please amend the paragraph at Page 10, line 20-Page 11, line 2, as follows: Referring now to Figure 2B, a phosphor-containing layer 220 is coated on the oblique sidewall 200d and also may be coated on the second face 200b. In some embodiments, the phosphor-containing layer may include a binder, such as an epoxy, a silicon-based matrix and/or other solvent. The phosphor may be cerium-doped YAG and/or other conventional phosphors. However, other conventional binders and/or phosphors may be used depending on the application. The phosphor may be coated on the LED by screen printing, evaporation (sputter, e-beam, thermal, CVD, electrostatic and/or electropheoric electrophoretic deposition), dipping, spin coating and/or other techniques. The phosphor-containing layer 220 then may be cured at between about 50°C and about 200°C for about several seconds to several hours. The thickness of the phosphor-containing layer 220 may range between about $2\mu m$ and about 100 µm, in some embodiments of the invention. However, other thicknesses may be used. The thickness that is used may be selected to reduce or minimize selfabsorption and/or scattering and may depend on the coating process, the density of the phosphor and/or the desired application. Moreover, a coating process or combinations of coatings processes may be selected to control the thickness of the phosphor on the oblique sidewall 200d compared to the second face 200b.